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Fast-response solar-blind ultraviolet photodetector with a

graphene/β-Ga₂O₃/graphene hybrid structure

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Abstract:

A high performance vertical solar-blind ultraviolet photodetector based on β -Ga₂O₃ thin films sandwiched between two graphene sheets has been fabricated by laser molecular beam epitaxy. The photodetector exhibits obvious rectifying characteristics and excellent solar-blind UV photoresponse. The fast rising and decay time of our detector are 0.96 s and 0.81 s under 254 nm illumination. The ratio of I_{254}/I_{dark} is up to 82.88 and the responsivity of graphene/ β -Ga₂O₃/graphene photodetector increases to 9.66 A/W at 10 V bias. Our results suggest that this performance is attributed to the existence of Schottky barriers between β -Ga₂O₃ and two graphene sheets. The combination of Ga₂O₃ and graphene might open up new possibilities for future UV integrated optoelectronic devices.

Keywords: Ga₂O₃, graphene, ultraviolet photodetector, laser molecular beam epitaxy technique

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